AMENDMENTS TO THE CLAIMS

Claims 1-4 (Canceled)

Claim 5 (Currently Amended): A method for operating a memory, comprising the steps of:

providing memory transistors arranged in a group of at least one of a row and a column;

providing a drive circuit coupled to a memory transistor of the group so that information can be written to and read from the memory transistor;

providing a selection transistor coupled with the group of memory transistors so that the group of memory transistors can be jointly selected;

~~opening~~ applying a high potential to the gate terminal of the selection transistor while gate terminals of the memory transistors of the group of memory transistors are at low potential;

measuring a first current flowing through each row or column to be read;

storing the measured first current;

supplying a read potential to gate terminals of the row or column to be read;

measuring a resulting second current flowing through the row or column to be read; and

comparing the second current with the stored first current.

Claim 6 (Currently Amended): A memory comprising:

means for providing memory transistors arranged in a group of at least one of a row and a column;

means for providing a drive circuit coupled to a memory transistor of the group so that information can be written to and read from the memory transistor;

means for providing a selection transistor coupled with the group of memory transistors so that the group of memory transistors can be jointly selected;

means for ~~opening~~ applying a high potential to the gate terminal of the selection transistor while gate terminals of the memory transistors of the group of memory transistors are at low potential;

means for measuring a first current flowing through each row or column to be read;

means for storing the measured first current;

means for supplying a read potential to gate terminals of the row or column to be read;

means for measuring a resulting second current flowing through the row or column to be read; and

means for comparing the second current with the stored first current.

Claim 7 (Currently Amended): A method for operating a memory having memory transistors arranged in a group, a drive circuit coupled to a memory transistor of the group so that information can be written to and read from the memory transistor, and a selection transistor coupled with the group of memory transistors so that the group of memory transistors can be jointly selected, the method comprising the steps of:

~~opening~~ applying a high potential to the gate terminal of the selection transistor while gate terminals of the memory transistors of the group of memory transistors are at low potential;

measuring a first current flowing through each row or column to be read;

storing the measured first current;

supplying a read potential to gate terminals of the row or column to be read;

measuring a resulting second current flowing through the row or column to be read; and

comparing the second current with the stored first current.